

Fig. 1

Fig. 2A

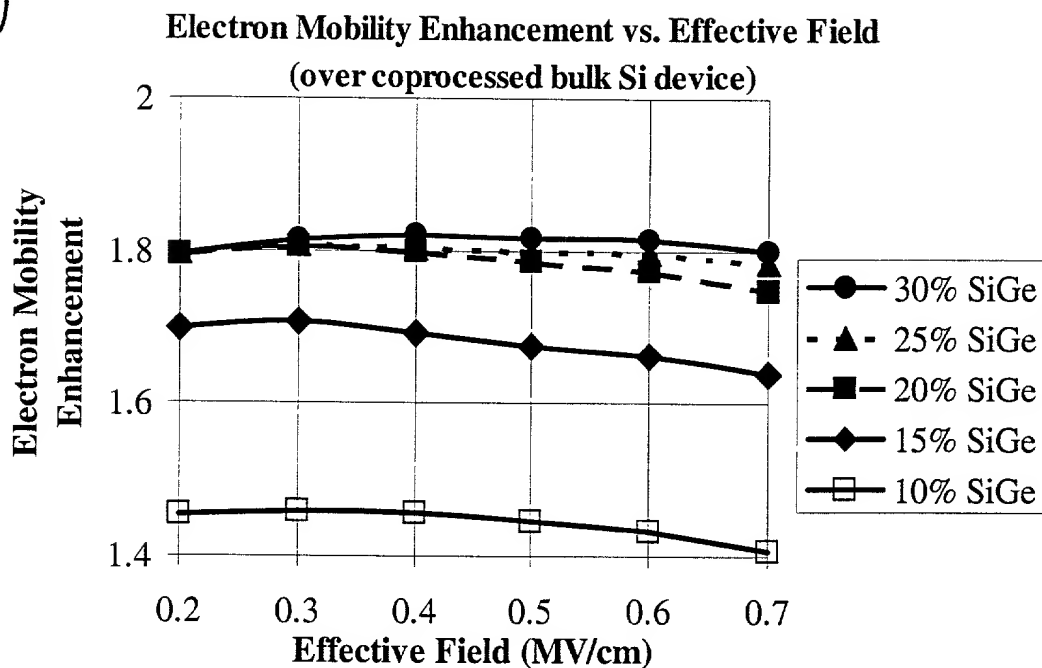
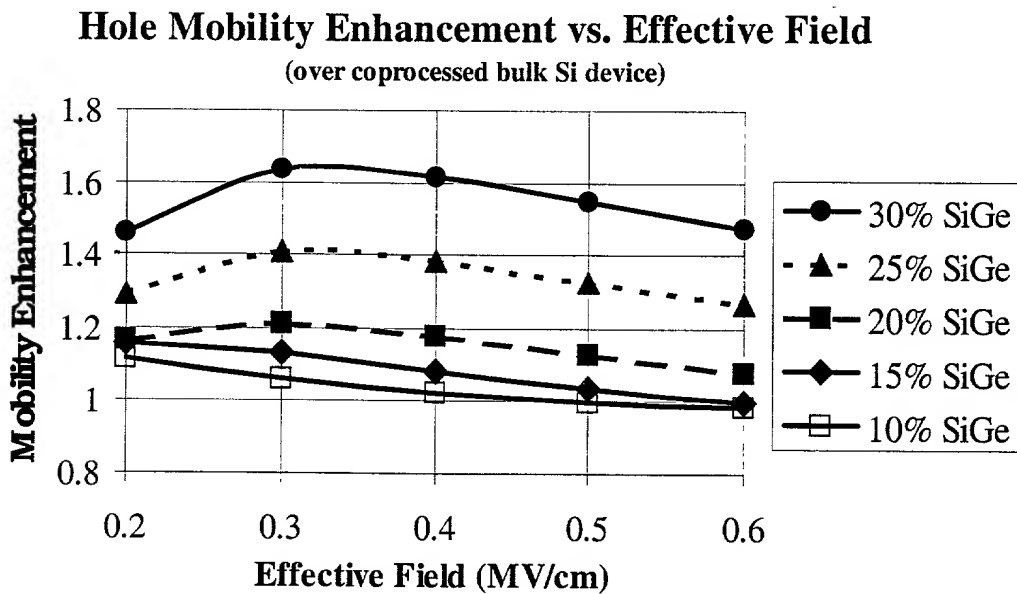


Fig. 2B



Type of Surface	Average Roughness (nm)
As-grown graded composition relaxed SiGe	7.9
Planarized SiGe	0.57
Regrowth SiGe	~0.6

Fig. 3

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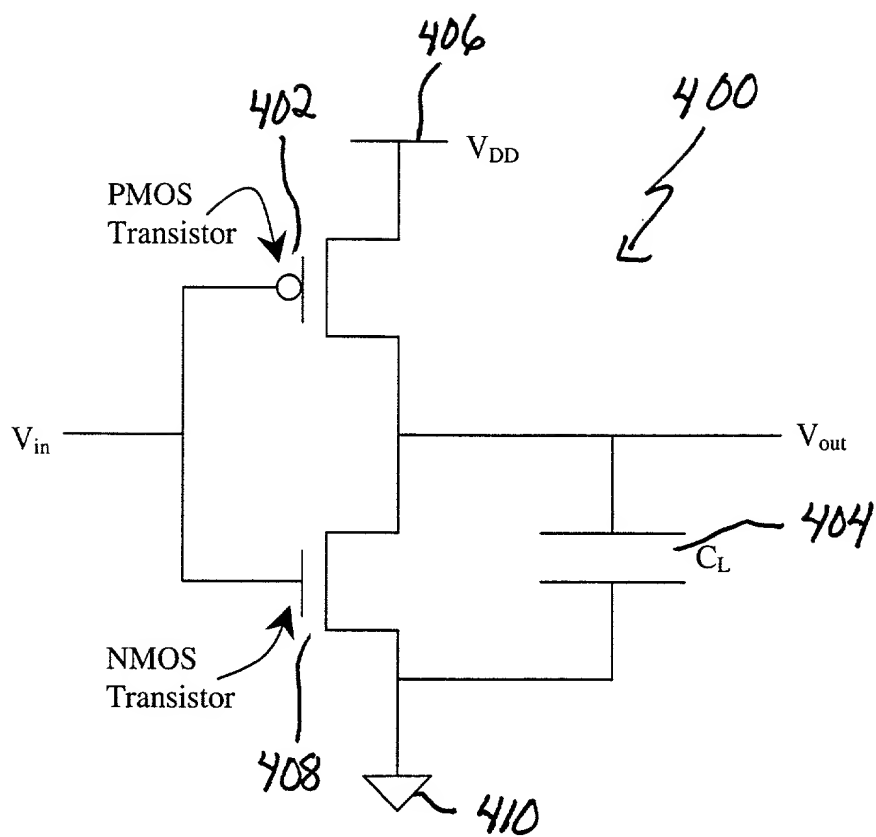


Fig. 4

Fig. 5A

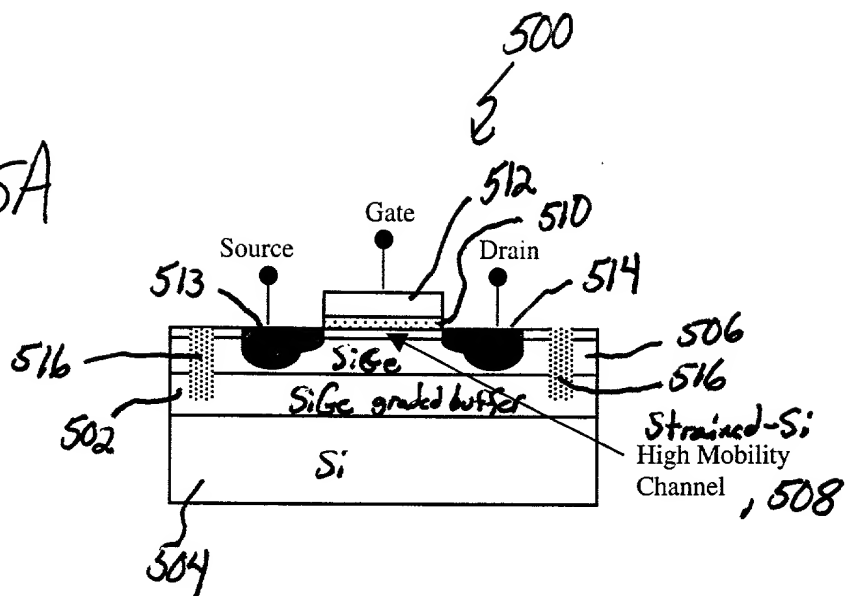
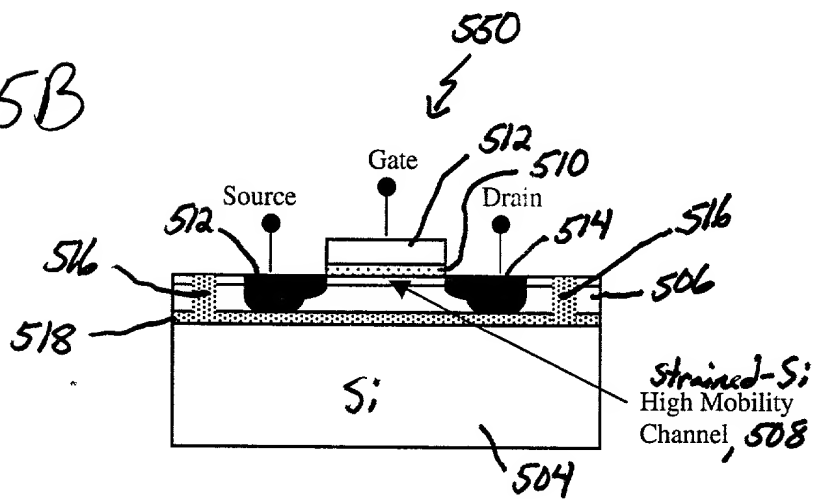


Fig. 5B



	n enhancement	p enhancement
$\text{Si}_{0.8}\text{Ge}_{0.2}$	1.75	1
$\text{Si}_{0.7}\text{Ge}_{0.3}$	1.8	1.4

Fig. 6

	Bulk Silicon	Strained-Si on 20% SiGe: High Speed	Strained-Si on 30% SiGe: High Speed	Strained-Si on 20% SiGe: Low Power	Strained-Si on 30% SiGe: Low Power
n enhancement	1	1.75	1.8	1.75	1.8
p enhancement	1	1	1.4	1	1.4
W_p (μm)	5.4	5.4	5.4	5.4	5.4
W_n (μm)	1.8	1.8	1.8	1.8	1.8
L_n, L_p (μm)	1.2	1.2	1.2	1.2	1.2
C_L (fF)	32	32	32	32	32
V_{DD} (V)	5	4.7	4.4	4.3	3.8
NM_H (V)	2.053	2.218	1.949	2.037	1.682
NM_L (V)	2.067	1.654	1.721	1.542	1.504
t_{pHL} (psec)	211.3	133.7	141.6	152.2	180.1
t_{pLH} (psec)	195.8	220.0	173.3	254.8	226.9
t_p (psec)	203.5	176.9	157.4	203.5	203.5
Power (mW)	3.93	3.93	3.93	2.87	2.21
% Speed Increase	-	15.1%	29.3%	-	-
% Power Reduction	-	-	-	27.0%	43.7%

Fig. 7

	Bulk Silicon	Strained-Si on 20% SiGe: Constant V_{DD}	Strained-Si on 30% SiGe: Constant V_{DD}	Strained-Si on 20% SiGe: High Speed Symmetrical Inverter	Strained-Si on 30% SiGe: High Speed Symmetrical Inverter	Strained-Si on 20% SiGe: Low Power Symmetrical Inverter	Strained-Si on 30% SiGe: Low Power Symmetrical Inverter
n enhancement	1	1.75	1.8	1.75	1.8	1.75	1.8
p enhancement	1	1	1.4	1	1.4	1	1.4
W_p (μm)	5.4	5.4	5.4	9.45	6.94	9.45	6.94
W_n (μm)	1.8	1.8	1.8	1.8	1.8	1.8	1.8
L_n, L_p (μm)	1.2	1.2	1.2	1.2	1.2	1.2	1.2
C_L (fF)	32	32	32	32	32	32	32
V_{DD} (V)	5	5	5	4.3	4.2	3.5	3.5
NM_{IH} (V)	2.053	2.376	2.198	1.782	1.770	1.5018	1.4796
NM_{IL} (V)	2.067	1.751	1.923	1.794	1.781	1.5101	1.4876
t_{pHL} (psec)	211.3	120.7	117.4	152.0	149.5	204.4	204.1
t_{pLH} (psec)	195.8	195.8	139.9	145.4	143.3	202.6	202.9
t_p (psec)	203.5	158.3	128.6	148.7	146.4	203.5	203.5
Power (mW)	3.93	5.06	6.22	3.93	3.93	1.95	1.89
% Speed Increase	-	28.6%	58.3%	36.9%	39.0%	-	-
% Power Reduction	-	-	-	-	-	50.4%	52.0%

Fig. 8

	Bulk Silicon	Strained-Si on 20% SiGe: High Speed	Strained-Si on 30% SiGe: High Speed	Strained-Si on 20% SiGe: Low Power	Strained-Si on 30% SiGe: Low Power
n enhancement	1	1.75	1.8	1.75	1.8
p enhancement	1	1	1.4	1	1.4
W_p (μm)	3.11	4.12	3.53	4.12	3.53
W_n (μm)	1.8	1.8	1.8	1.8	1.8
L_n, L_p (μm)	1.2	1.2	1.2	1.2	1.2
C_L (fF)	22.5	26.7	24.2	26.7	24.2
V_{DD} (V)	5	4.5	4.3	4.4	3.8
NM_H (V)	2.370	2.275	2.123	2.220	1.872
NM_L (V)	1.756	1.485	1.511	1.458	1.371
t_{pHL} (psec)	148.4	117.3	109.3	121.5	132.4
t_{pLH} (psec)	238.5	254.8	204.9	265.3	254.4
t_p (psec)	193.4	186.0	157.1	193.4	193.4
Power (mW)	2.90	2.90	2.90	2.66	1.83
% Speed Increase	-	4.0%	23.1%	-	-
% Power Reduction	-	-	-	8.4%	37.1%

Fig. 9

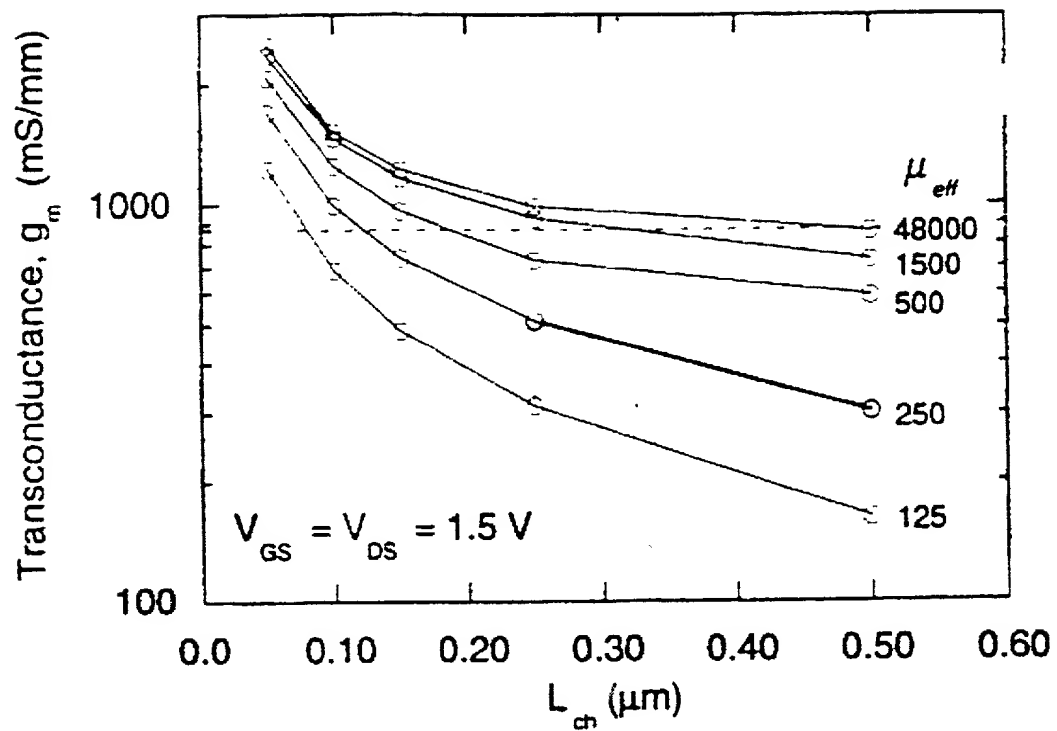


Fig. 10

ϵ -Si Effect on t_p for 0.25 μ m Inverter

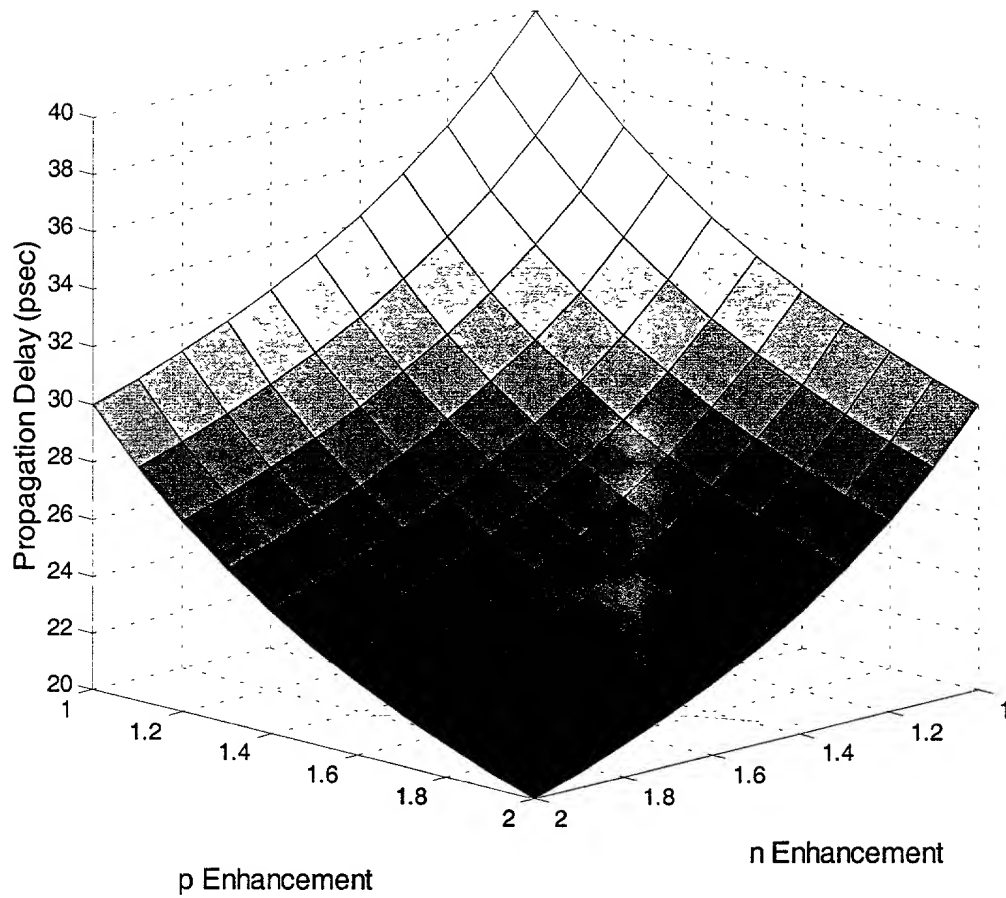


Fig. 11

Fig. 12A

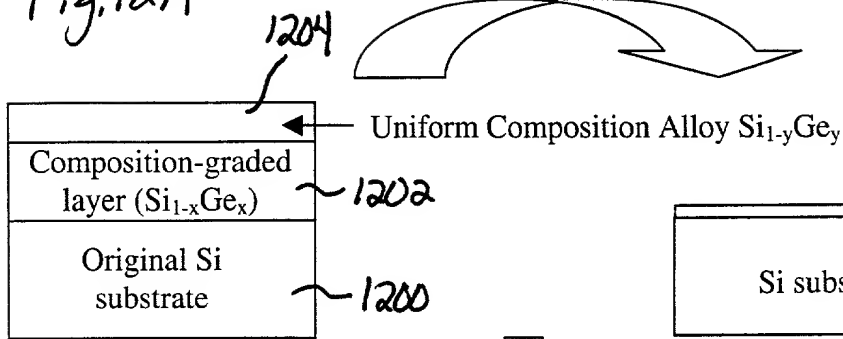


Fig. 12B

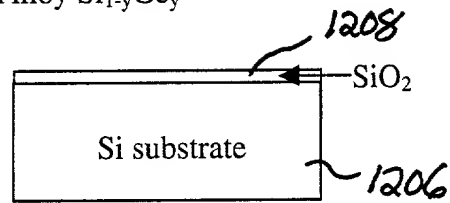


Fig. 12C

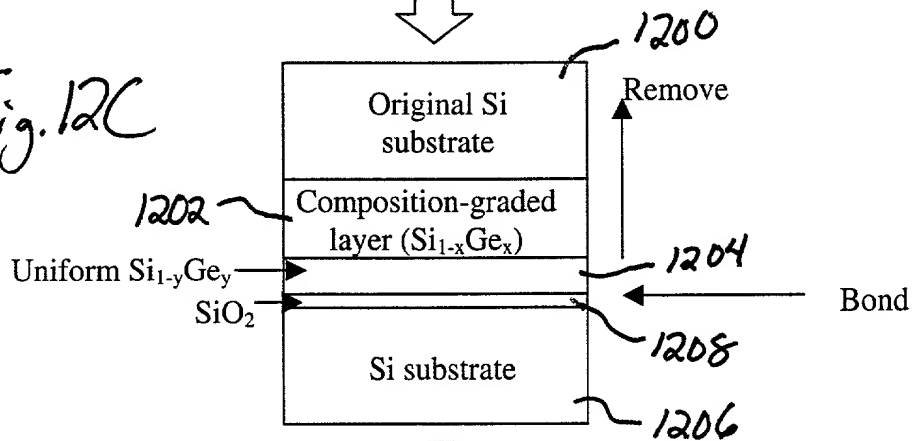


Fig. 12D

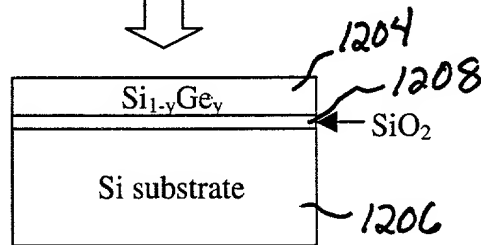


Fig. 12E

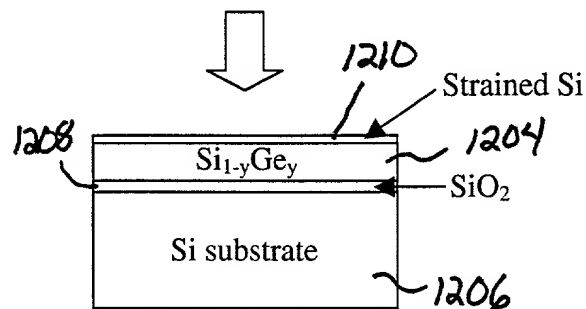


Fig. 13A

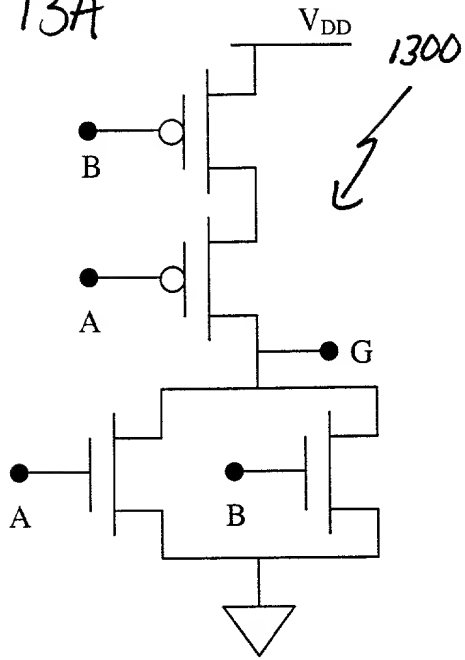


Fig. 13B

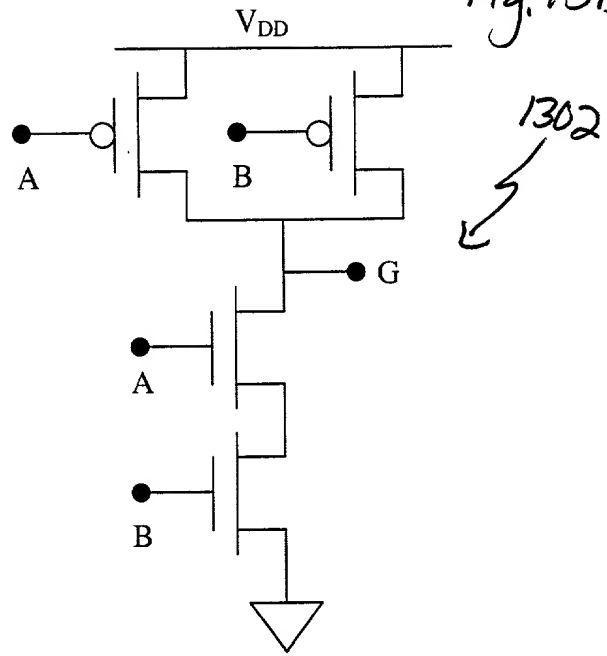


Fig. 13C

